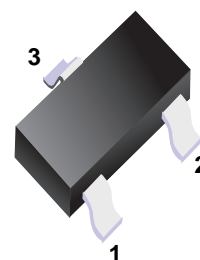


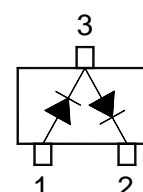
Silicon Epitaxial Schottky Barrier Diode

■ Features

- High reliability
- Low reverse current



■ Simplified outline(SOT-323)



■ Marking

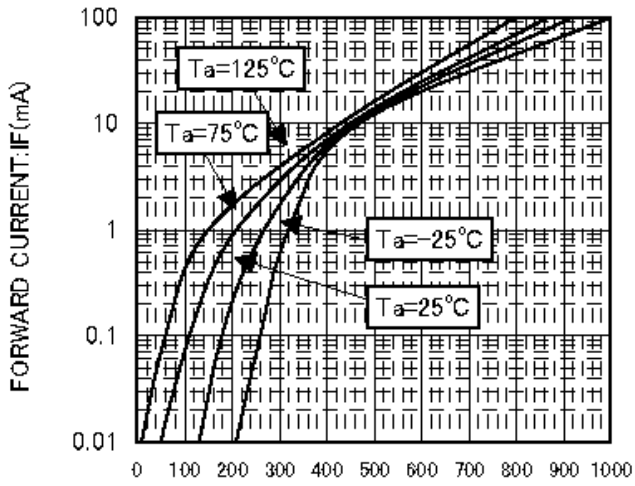
| | |
|---------|----|
| Marking | 3J |
|---------|----|

■ Absolute Maximum Ratings Ta = 25°C

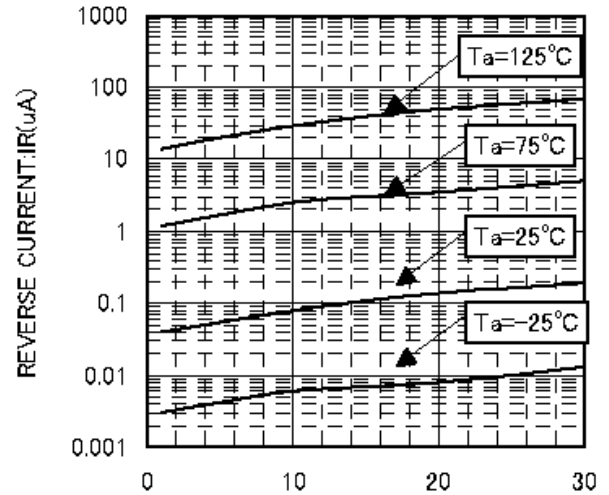
| Parameter | Symbol | Value | Unit |
|---|-------------|---------------|------|
| Repetitive Peak Reverse Voltage | V_{RM} | 45 | V |
| Reverse Voltage | V_R | 40 | V |
| Average Forward Rectified Current | $I_{F(AV)}$ | 30 | mA |
| Peak Forward Surge Current (t = 8.3 ms) | I_{FSM} | 200 | mA |
| Junction Temperature | T_j | 125 | °C |
| Storage Temperature Range | T_{stg} | - 55 to + 125 | °C |

■ Electrical Characteristics Ta = 25°C

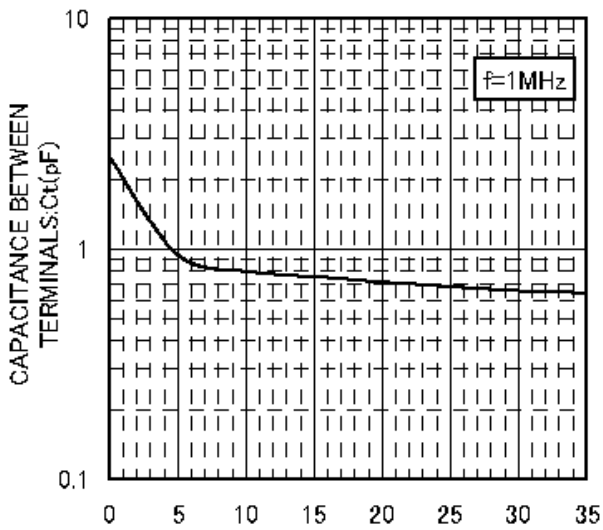
| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--|-------------|------|------|------|------|
| Forward Voltage at $I_F = 1$ mA | V_F | - | - | 0.37 | V |
| Reverse Current at $V_R = 10$ V | I_R | - | - | 1 | μA |
| Reverse Breakdown Voltage at $I_R = 10$ μA | $V_{(BR)R}$ | 45 | - | - | V |
| Capacitance between Terminals at $V_R = 1$ V, f = 1 MHz | C_T | - | 2 | - | pF |



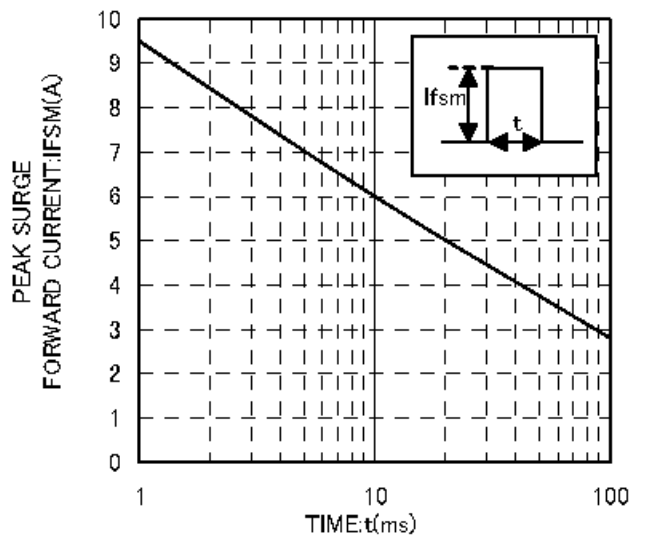
FORWARD VOLTAGE: VF(mV)
VF-IF CHARACTERISTICS



REVERSE VOLTAGE: VR(V)
VR-IR CHARACTERISTICS

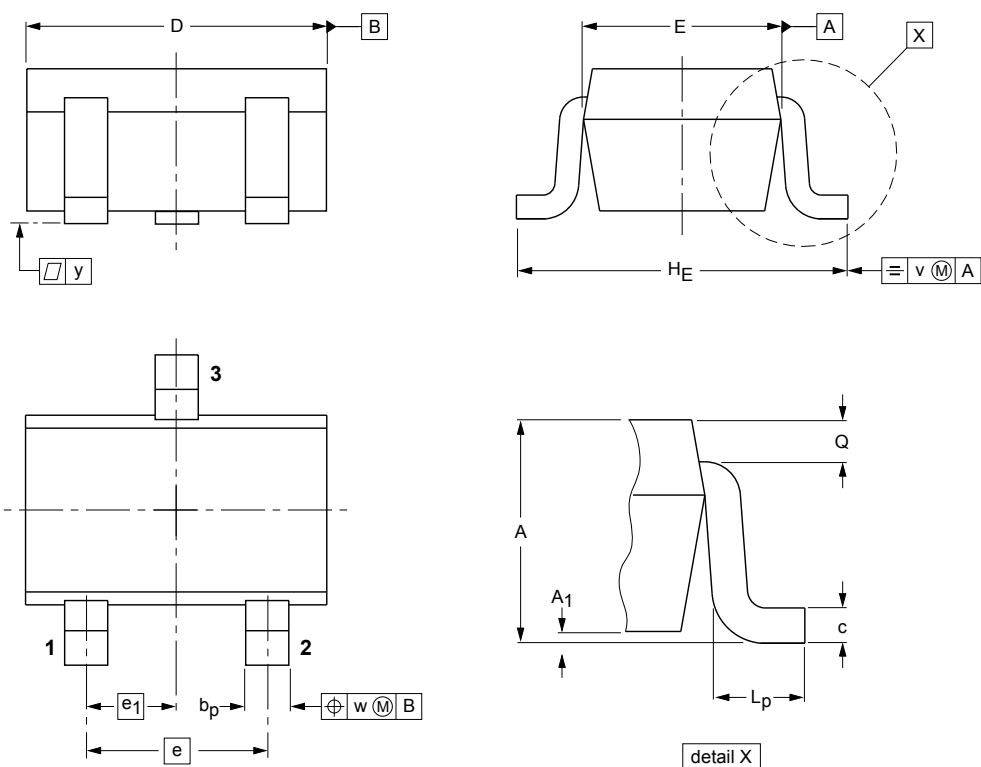


REVERSE VOLTAGE: VR(V)
VR-Ct CHARACTERISTICS



IFSM-t CHARACTERISTICS

■ SOT-323



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ max | b _p | c | D | E | e | e ₁ | H _E | L _p | Q | v | w |
|------|------------|-----------------------|----------------|--------------|------------|--------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm | 1.1 0.8 | 0.1 | 0.4 0.3 | 0.25 0.10 | 2.2 1.8 | 1.35 1.15 | 1.3 | 0.65 | 2.2 2.0 | 0.45 0.15 | 0.23 0.13 | 0.2 | 0.2 |